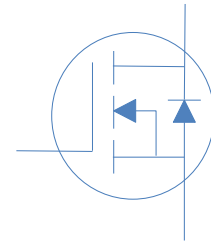


**100V N-Ch Power MOSFET**

$V_{DS}$	100	V
$R_{DS(on),typ}$ $V_{GS}=10V$	17.5	m
$I_D$ (Silicon Limited)	20	A

Part Number	Package	Marking
HGA170N10A	TO-220F	GA170N10A


**Absolute Maximum Ratings at  $T_J=25^{\circ}C$  (unless otherwise specified)**

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25^{\circ}C$	20	A
		$T_C=100^{\circ}C$	14	
Drain to Source Voltage	$V_{DS}$	-	100	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 20$	V
Pulsed Drain Current	$I_{DM}$	-	180	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=0.4mH, T_C=25^{\circ}C$	45	mJ
Power Dissipation	$P_D$	$T_C=25^{\circ}C$	17	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 175	$^{\circ}C$

**Absolute Maximum Ratings**

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{JA}$	60	$^{\circ}C/W$
Thermal Resistance Junction-Case	$R_{JC}$	9	$^{\circ}C/W$



$V_{GS}$

Fig 1. Typical Output Characteristics

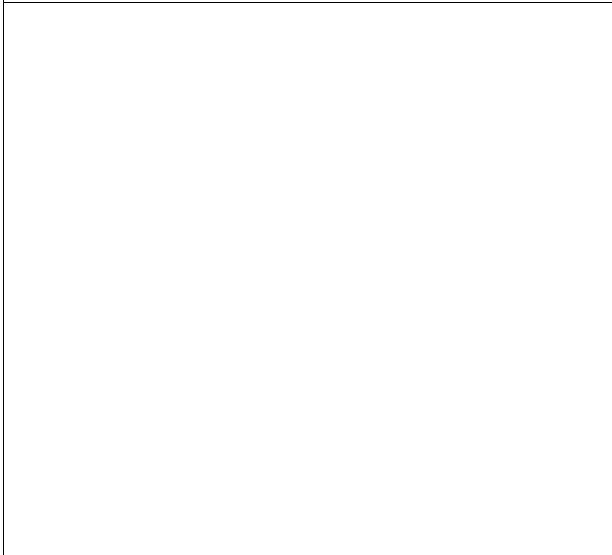


Figure 2. On-Resistance vs. Gate-Source Voltage

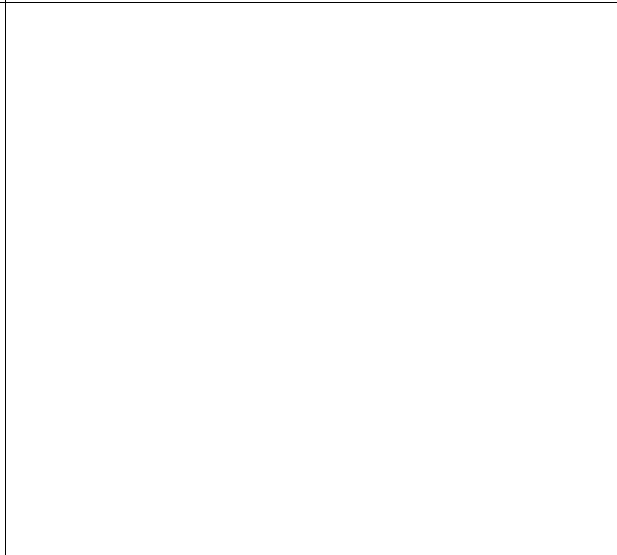


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

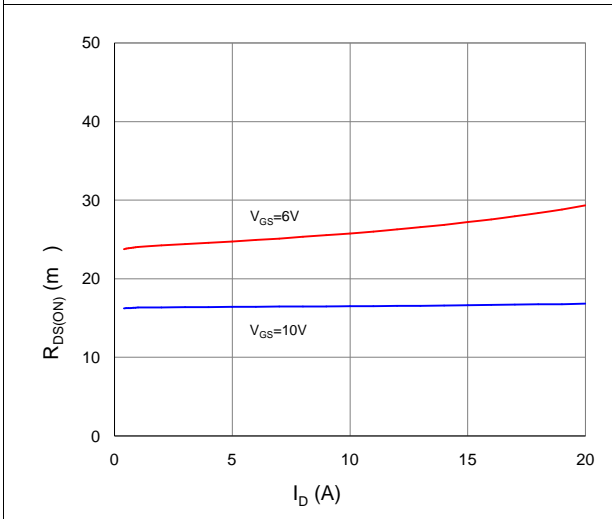


Figure 4. Normalized On-Resistance vs. Junction Temperature

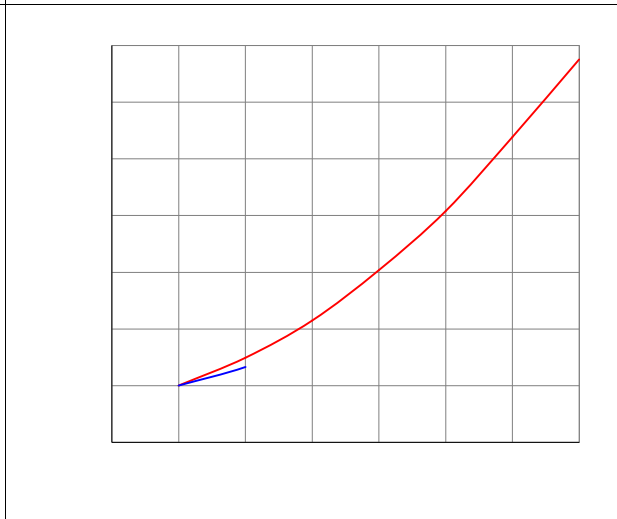


Figure 5. Typical Transfer Characteristics

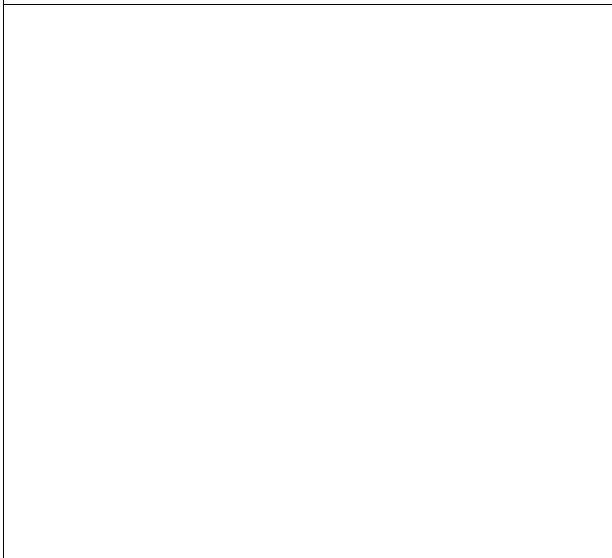


Figure 6. Typical Source-Drain Diode Forward Voltage

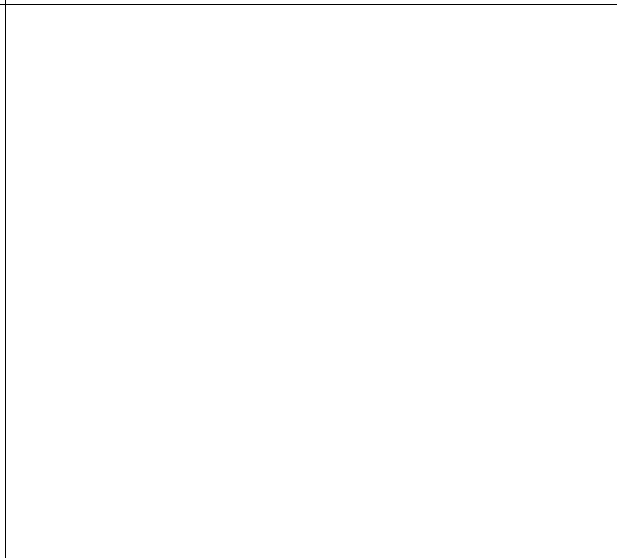


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

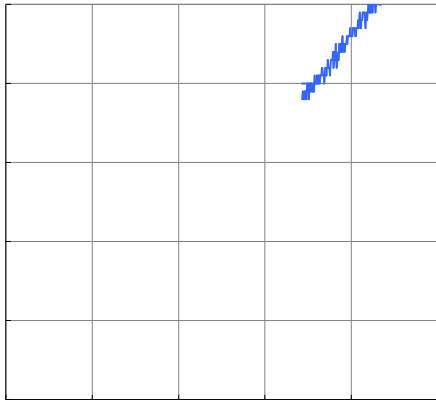


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

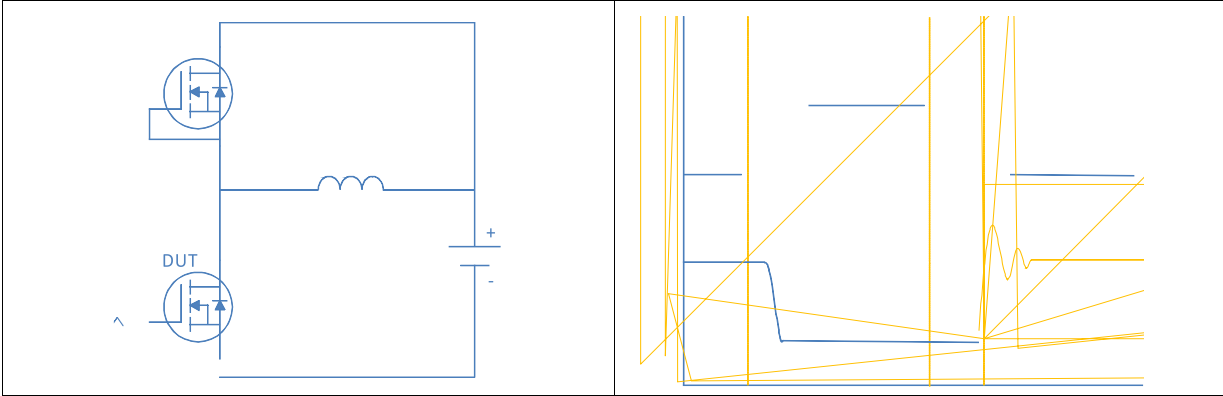
Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

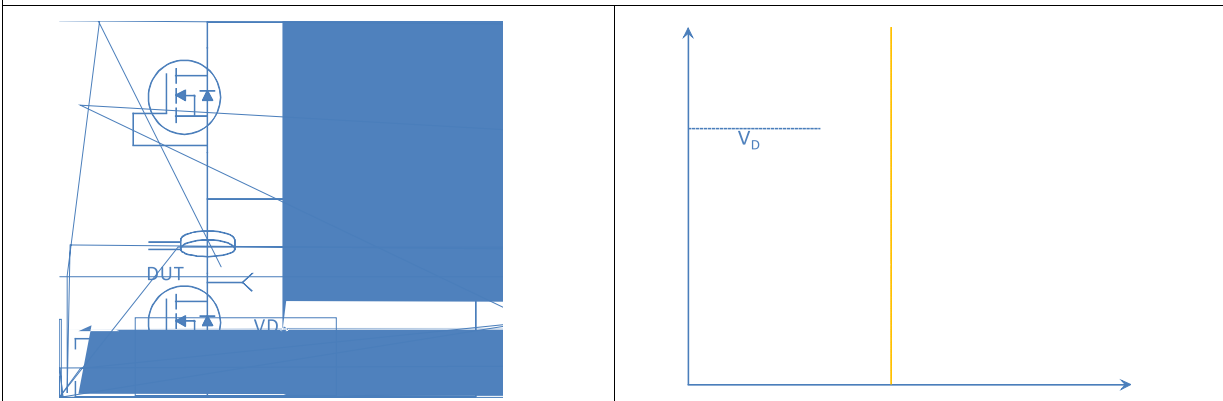
50

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

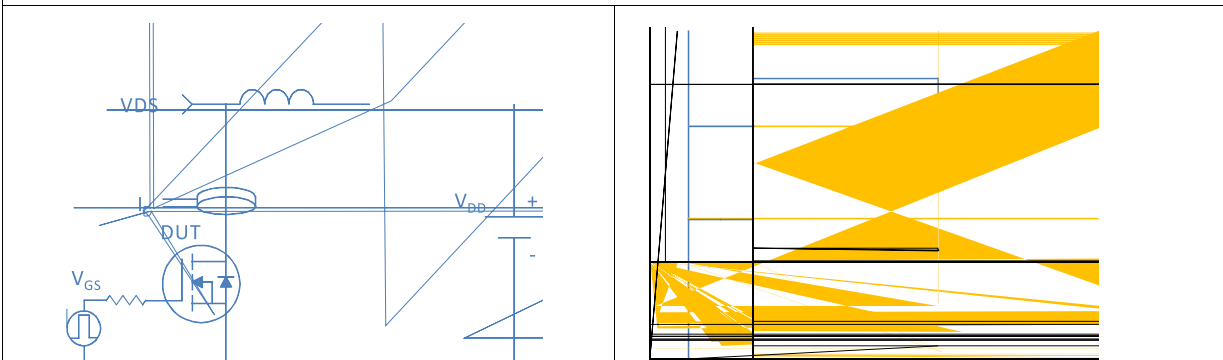
Inductive switching Test



Gate Charge Test



Uclamped Inductive Switching (UIS) Test



Diode Recovery Test

